



Description

JMT P-channel MOSFET

Features

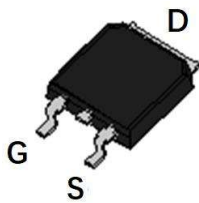
- $V_{DS} = -20V$, $I_D = -60A$
 $R_{DS(ON)} < 8.5m\Omega$ @ $V_{GS} = -4.5V$
 $R_{DS(ON)} < 12m\Omega$ @ $V_{GS} = -2.5V$
- High Power and Current Handling Capability
- Lead Free Product is Acquired
- Surface Mount Package

Application

- PWM Applications
- Load Switch



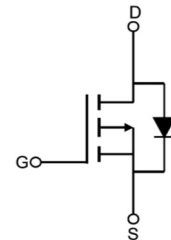
100% UIS TESTED!
100% ΔV_{ds} TESTED!



TO-252(DPAK) top view



Marking and pin Assignment



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	OUTLINE	Device Package	Reel Size	Reel (PCS)	Per Carton (PCS)
JMTK50P02A	JMTK50P02A	TAPING	TO-252	13inch	2500	25,000

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units
V _{DSS}	Drain-Source Voltage	-20	V
V _{GSS}	Gate-Source Voltage	±12	V
I _D	Continuous Drain Current	T _C = 25°C	-60
		T _C = 100°C	-39
I _{DM}	Pulsed Drain Current ^{note1}	-240	A
P _D	Power Dissipation	70	W
R _{θJC}	Thermal Resistance, Junction to Ambient	2.1	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C



Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-20	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -20V, V _{GS} = 0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±12V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-0.4	-0.85	-1.2	V
R _{DS(on)}	Static Drain-Source on-Resistance <small>note3</small>	V _{GS} =-4.5V, I _D =-15A	-	6.6	8.5	mΩ
		V _{GS} =-2.5V, I _D =-12A	-	8	12	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f = 1.0MHz	-	4590	-	pF
C _{oss}	Output Capacitance		-	505	-	pF
C _{rss}	Reverse Transfer Capacitance		-	440	-	pF
Q _g	Total Gate Charge	V _{DS} =-10V, I _D =-15A, V _{GS} =-4.5V	-	46	-	nC
Q _{gs}	Gate-Source Charge		-	7.3	-	nC
Q _{gd}	Gate-Drain("Miller") Charge		-	10	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =-10V, I _D =-14A, R _{GEN} =2.7Ω, V _{GS} =-10V	-	8	-	ns
t _r	Turn-on Rise Time		-	59	-	ns
t _{d(off)}	Turn-off Delay Time		-	111	-	ns
t _f	Turn-off Fall Time		-	43	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-60	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-240	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S =-20A	-	-	-1.2	V
trr	Reverse Recovery Time	T _J =25°C, I _{SD} =-15A,	-	18	-	ns
Qrr	Reverse Recovery Charge	V _{GS} =0V di/dt=-100A/μs	-	7.7	-	nC

- Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: T_J=25°C, V_{DD}=-10V, V_G=-10V, R_G=5.9Ω, L=0.5mh, I_{AS}=-13.2A
3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%



Typical Performance Characteristics

Figure 1: Output Characteristics

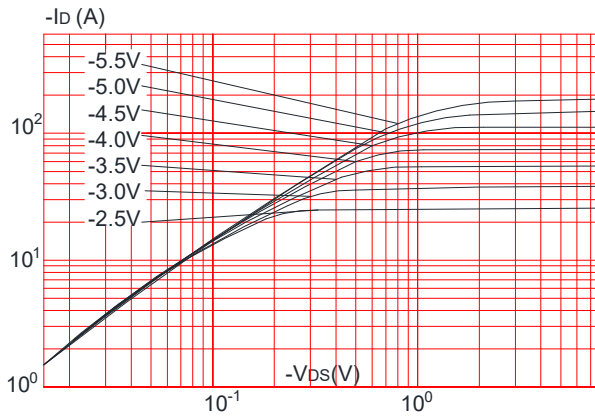


Figure 2: Typical Transfer Characteristics

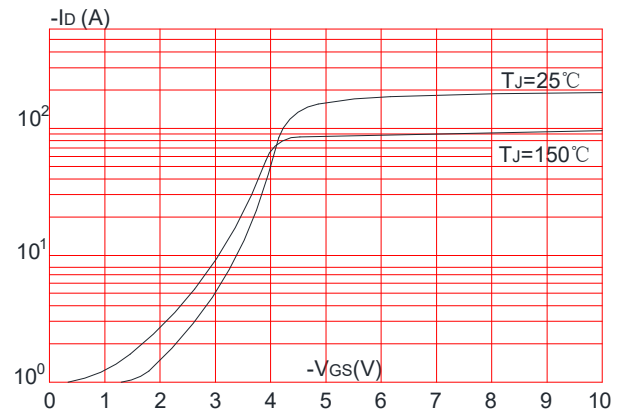


Figure 3: On-resistance vs. Drain Current

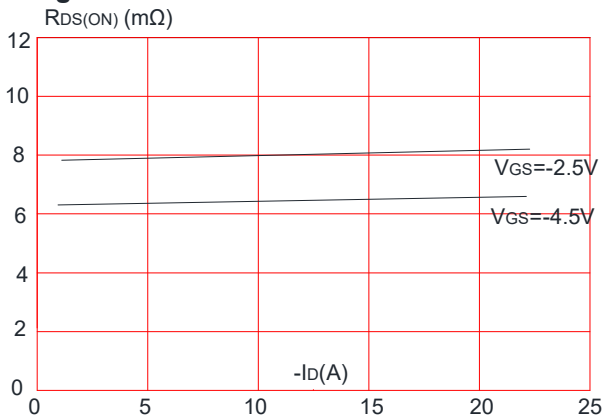


Figure 4: Body Diode Characteristics

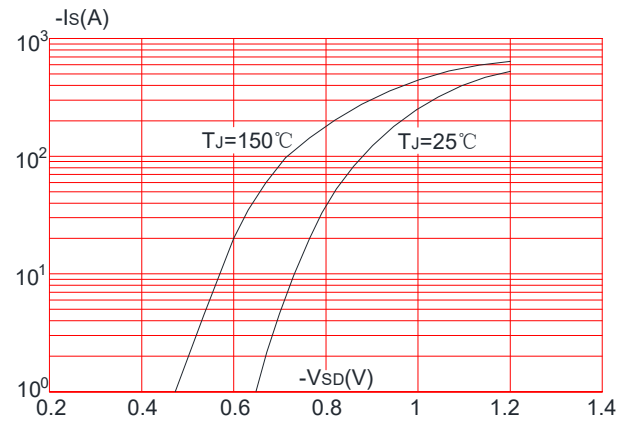


Figure 5: Gate Charge Characteristics

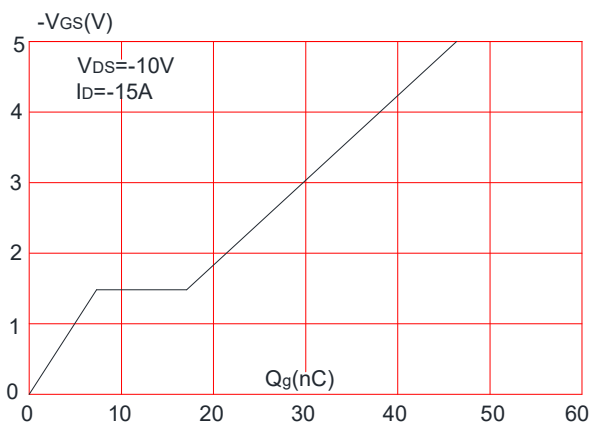


Figure 6: Capacitance Characteristics

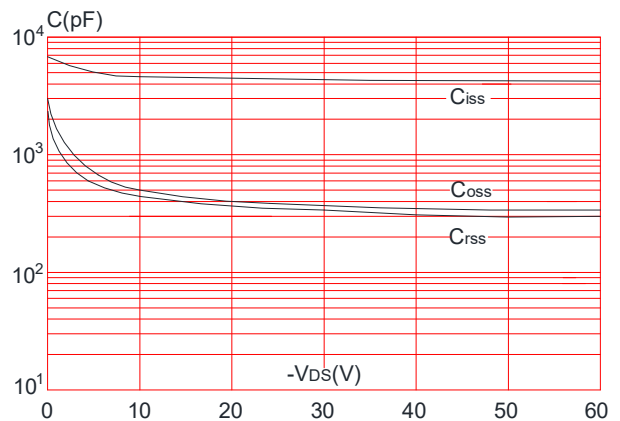




Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

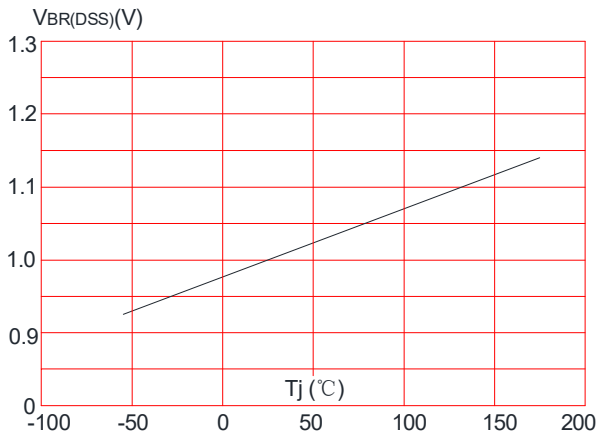


Figure 8: Normalized on Resistance vs. Junction Temperature

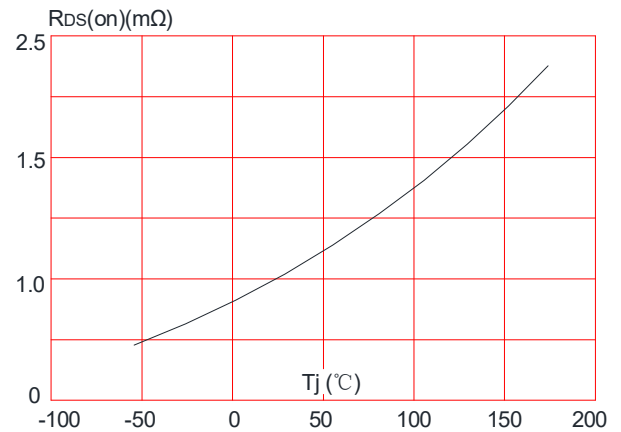


Figure 9: Maximum Safe Operating Area

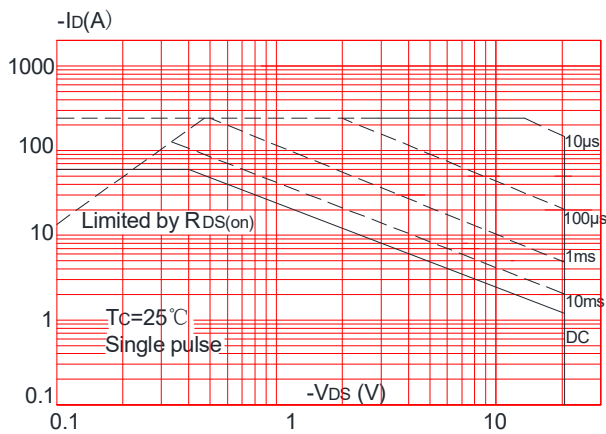


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

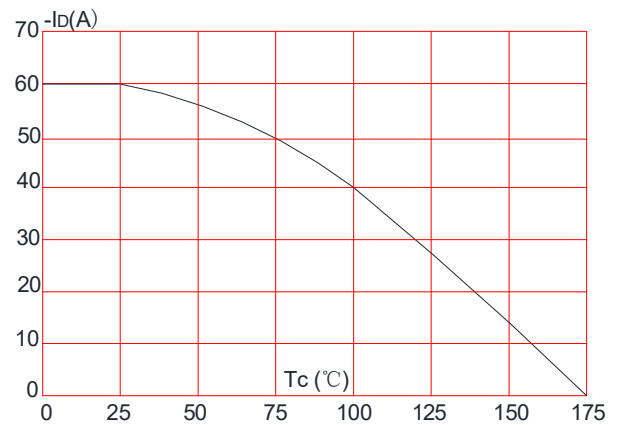
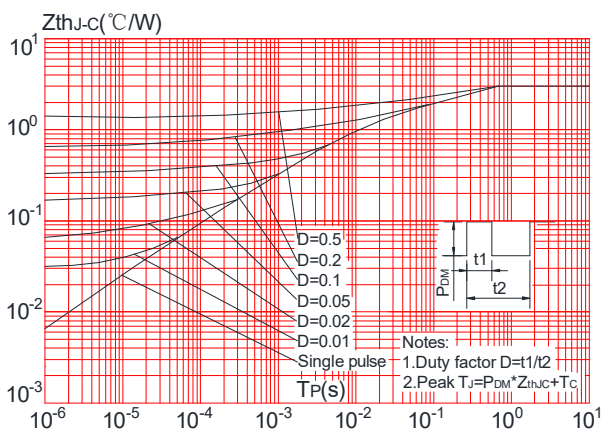


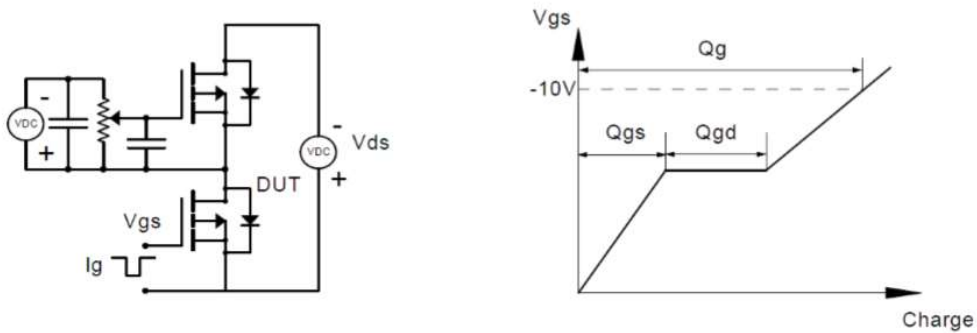
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



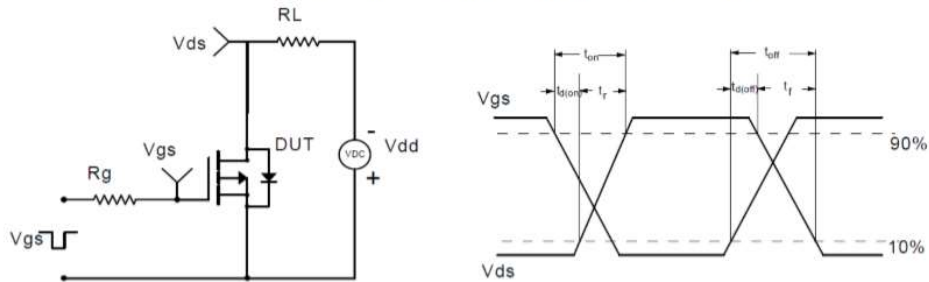
Test Circuit



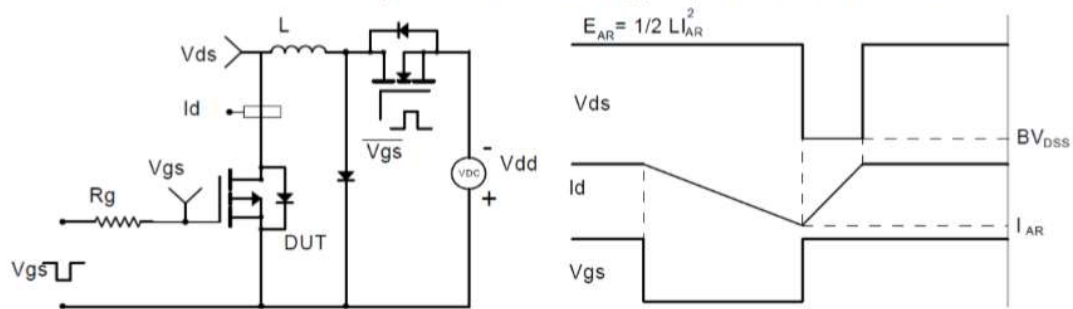
Gate Charge Test Circuit & Waveform



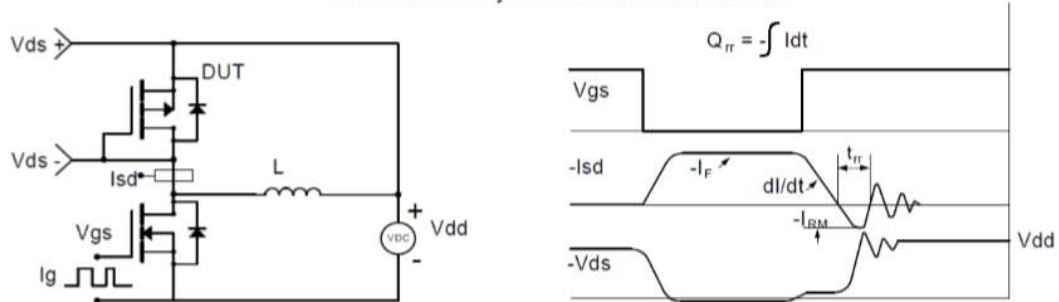
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



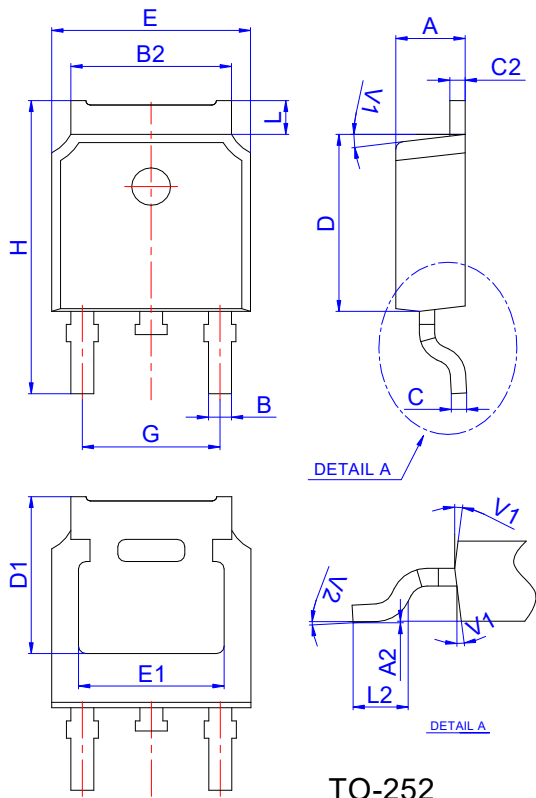
Diode Recovery Test Circuit & Waveforms



Package Mechanical Data

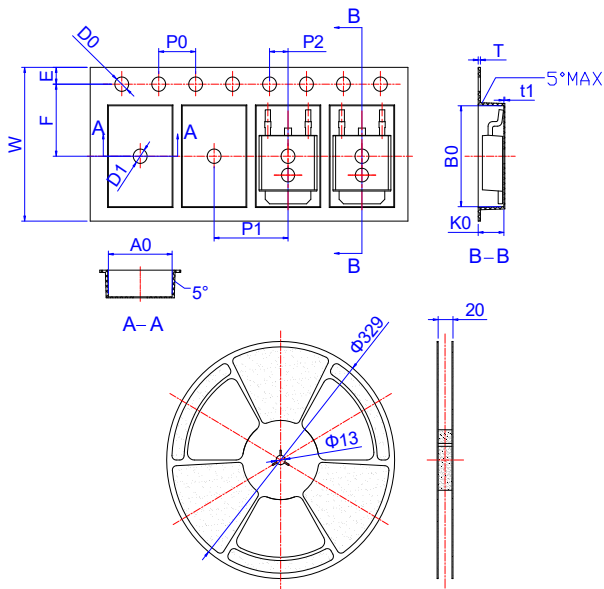


JMTK50P02A



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2		0°	6°	0°		6°

Reel Specification-TO-252




Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583



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